UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

: 7,273,533 B2

Page 1 of 1

APPLICATION NO.: 10/717268

DATED

: September 25, 2007

INVENTOR(S)

: Brcka et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page, (56) under the "References Cited" section, "6,685,799 B2* 2/2004 Hooshdaran et al." should read --6,685,799 B2* 2/2004 Davis et al.--.

Col. 2, line 31, "torroids," should read --toroids,--.

Col. 2, line 35, "by the present applicant" should read -- by the present applicants--.

Col. 2, line 39, "are becoming of increase demand" should read -- are becoming of increased demand--.

Col. 2, line 51, "processing of 300 mm wafer." should read --processing of 300 mm wafers .--.

Col. 5, line 4, "low flux channels, are" should read --low flux channels are--.

Col. 8, line 23, "Applicant has proposed" should read -- Applicants have proposed--.

Col. 10, line 3, "of the rf power deposited into" should read -- of the RF power deposited into--.

Col. 10, line 45, "(FIG. 2O and 2F)" should read --(FIGS. 2D and 2F)--.

Signed and Sealed this

Eleventh Day of November, 2008

JON W. DUDAS Director of the United States Patent and Trademark Office